

MULTIPLE DIELECTRIC FINFET STRUCTURE AND METHOD

Abstract

Disclosed is a method and structure for a fin-type field effect transistor (FinFET) structure that has different thickness gate dielectrics covering the fins extending from the substrate. These fins have a central channel region and source and drain regions on opposite sides of the channel region. The thicker gate dielectrics can comprise multiple layers of dielectric and the thinner gate dielectrics can comprise less layers of dielectric. A cap comprising a different material than the gate dielectrics can be positioned over the fins.